

SIDC07D60F6

Fast switching diode

Features:

- 600V Emitter Controlled technology 70 μm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

 power modules and discrete devices



Applications:

 SMPS, resonant applications, drives

Chip Type	V_{R}	I _F	Die Size	Package
SIDC07D60F6	600V	22.5A	2.12 x 3.41 mm ²	sawn on foil

Mechanical Parameters

Anode pad size 1.638 x 2.928 Thickness 70 μm Wafer size 150 mm Max. possible chips per wafer 2000 Passivation frontside Photoimide Pad metal 3200 nm AlSiCu Ni Ag −system suitable for epoxy and soft solder die bonding Die bond Electrically conductive glue or solder Wire bond Al, ≤250μm Reject ink dot size Ø 0.65mm; max 1.2mm Store in original container, in dry nitrogen, in dark	Meditalical Farameters			
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Passivation frontside Photoimide Pad metal 3200 nm AlSiCu Backside metal Ni Ag –system suitable for epoxy and soft solder die bonding Die bond Electrically conductive glue or solder Wire bond Al, ≤250μm Reject ink dot size Ø 0.65mm; max 1.2mm Store in original container, in dry nitrogen, in dark	Wafer size	150	mm	
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Wire bond AI, ≤250μm Reject ink dot size Ø 0.65mm; max 1.2mm Store in original container, in dry nitrogen, in dark	Backside metal			
Reject ink dot size Ø 0.65mm; max 1.2mm Store in original container, in dry nitrogen, in dark	Die bond	Electrically conductive glue or solder		
Recommended storage environment Store in original container, in dry nitrogen, in dark	Wire bond	AI, ≤250μm		
	Reject ink dot size	Ø 0.65mm; max 1.2mm		
	Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C		



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	V_{RRM}	<i>T</i> _{vj} = 25 °C	600	V	
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	۸	
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150°C	45	- A	
Junction temperature range	T _{vj}		-40+175	°C	
Operating junction temperature	T _{vj}		-40+150	°C	
Dynamic ruggedness ²⁾	P _{max}	$I_{\text{Fmax}} = 45\text{A}, \ V_{\text{Rmax}} = 600\text{V}, \ T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW	

¹⁾ depending on thermal properties of assembly

Static Characteristic (tested on wafer), T_{vj} = 25 °C

Parameter	Symbol	Conditions	Value			Unit
raiailletei		Conditions	min.	typ.	max.	Oilit
Reverse leakage current	I_{R}	V _R =600V			27	μA
Cathode-Anode breakdown Voltage	V_{BR}	I _R =1.5mA	600			V
Diode forward voltage	V _F	I _F =22.5A		1.6		V

Further Electrical Characteristics

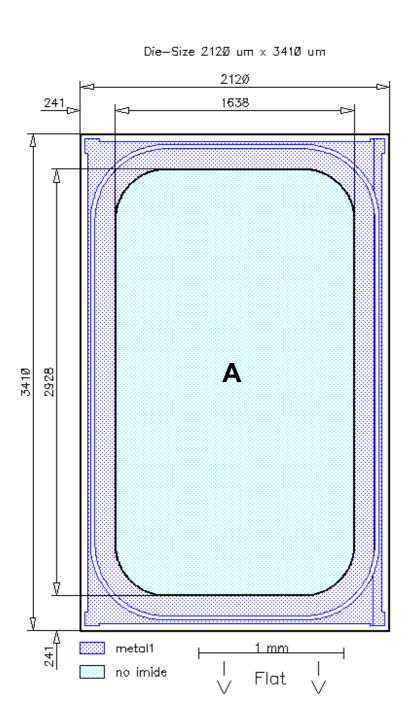
Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

²⁾ not subject to production test - verified by design/characterisation





Chip Drawing



A: Anode pad



SIDC07D60F6

Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

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